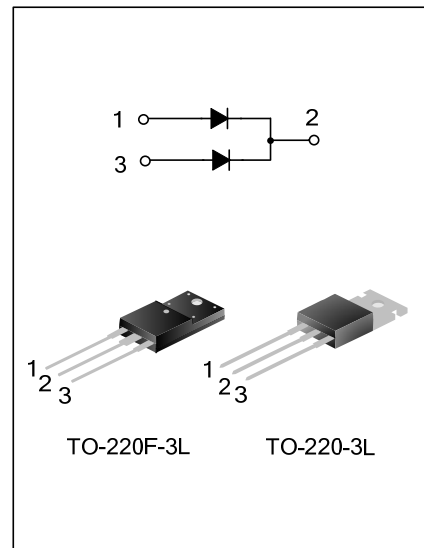


## 16A, 400V SUPER-FAST RECOVERY RECTIFIER

### GENERAL DESCRIPTION

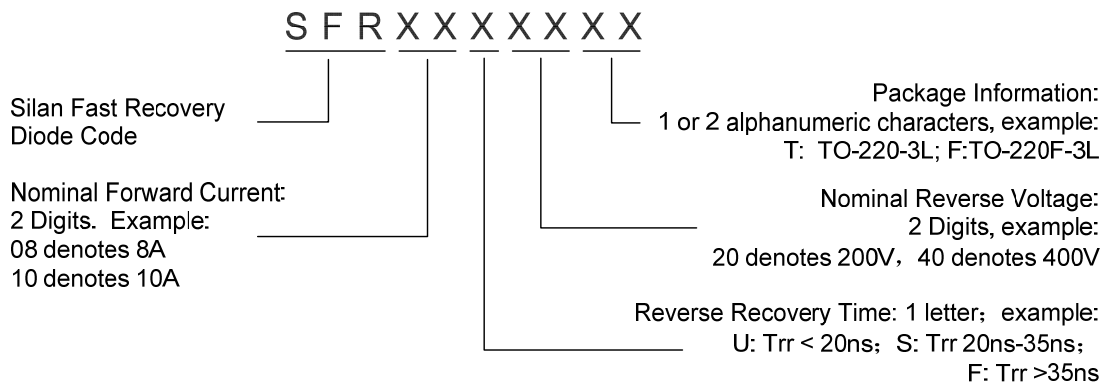
SFR16S40T/F is a Super-Fast Recovery Diode, fabricated in advanced silicon planar epitaxial technology. The process parameter and the device structure are fine tuned with optimized performance of forward voltage drop and reverse recovery time. Accuracy epitaxial dope control, advanced planar junction terminal structure and the platinum doped life control, guarantee the best overall performance, ruggedness and reliability characteristics. SFR16S40T/F is intended for use in the output rectification stage of SMPS, UPS, DC-DC converters as well as free-wheeling diode in low voltage inverters and chopper motor drivers.



### FEATURES

- \* Ultrafast 35 Nanosecond Recovery Time
- \* Low Forward Voltage Drop
- \* Low Leakage Current
- \* 175 °C Operating Junction Temperature

### NOMENCLATURE



### ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SFR16S40T	TO-220-3L	SFR16S40T	Pb free	Tube
SFR16S40F	TO-220F-3L	SFR16S40F	Pb free	Tube

## ABSOLUTE MAXIMUM RATINGS

Characteristics	Symbol	Ratings	Unit
Peak Repetitive Reverse Voltage	VRRM	400	V
Average Rectified Forward Current	IF(AV)	8.0	A
Per Leg		16	
Total Device			
Non Repetitive Peak Surge Current	IFSM	100	A
Per Leg			
Operation Junction Temperature	TJ	-40~+175	°C
Storage Temperature	Tstg	-65~+175	°C

## THERMAL CHARACTERISTICS(Per Leg)

Characteristics	Symbol	Ratings	Unit
Thermal Resistance, Junction-to-Case	R $\theta$ JC	3.0	°C/W

## ELECTRICAL CHARACTERISTICS(Per Leg)

Characteristics	Symbol	Min.	Typ.	Max.	Unit
Maximum Instantaneous Forward Voltage (Note 1)	VF	--	--	1.03	V
(IF=8.0 Amps, Tc=150°C)				1.25	
(IF=8.0 Amps, Tc=25°C)					
Maximum Instantaneous Reverse Current(Note 1)	IR	--	--	250	$\mu$ A
(Rated dc Voltage, Tc=150°C)				5.0	
(Rated dc Voltage, Tc=25°C)					
Maximum Reverse Recovery Time	trr	--	--	35	ns
(IF=1.0 Amp, di/dt=50Amps/ $\mu$ S)				25	
(IF=0.5 Amp, IR=1.0Amp, IREC=0.25Amp)					

Notes:

1. Pulse Test: Pulse Width=300 $\mu$ S, Duty Cycle $\leq$ 2.0%

**TYPICAL CHARACTERISTICS**

Figure 1. Instantaneous reverse leakage current vs. Percent of rated peak reverse voltage

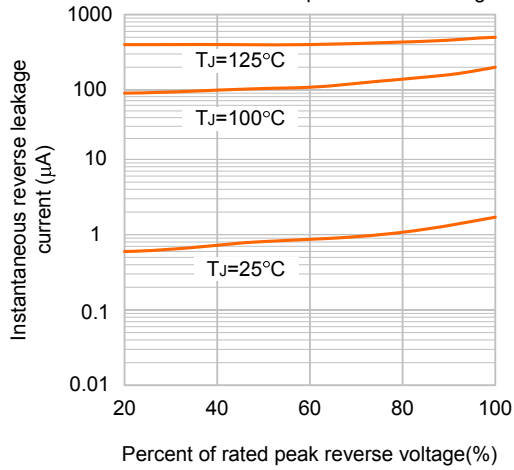


Figure 2. Junction capacitance vs. Reverse voltage

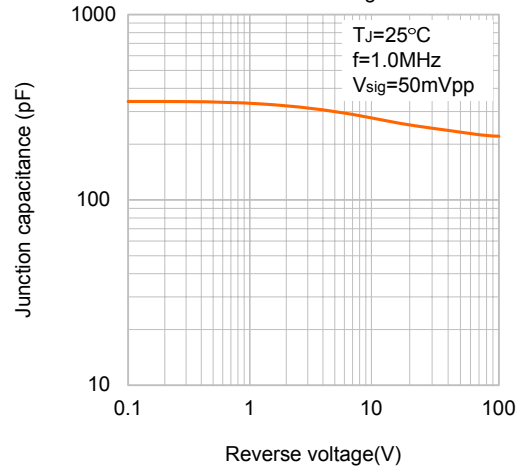
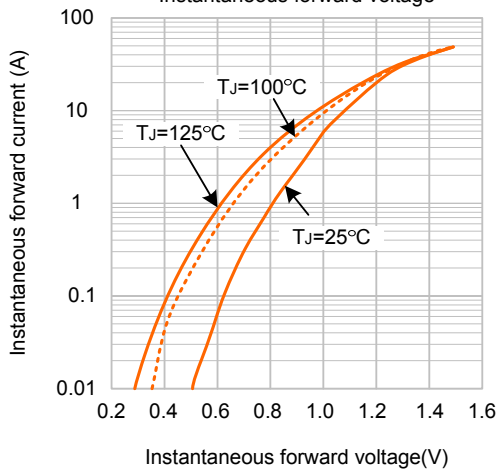


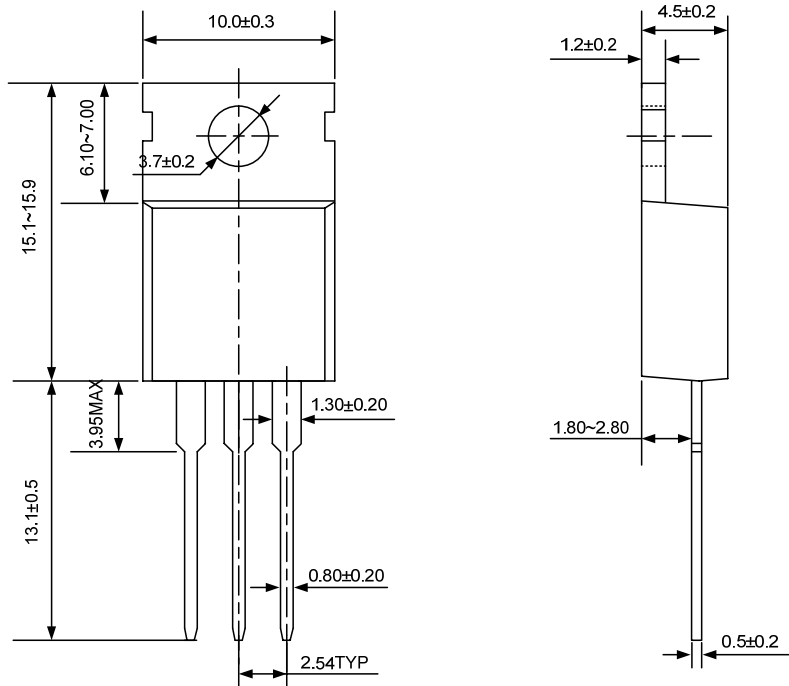
Figure 3. Instantaneous forward current vs. Instantaneous forward voltage



**PACKAGE OUTLINE**

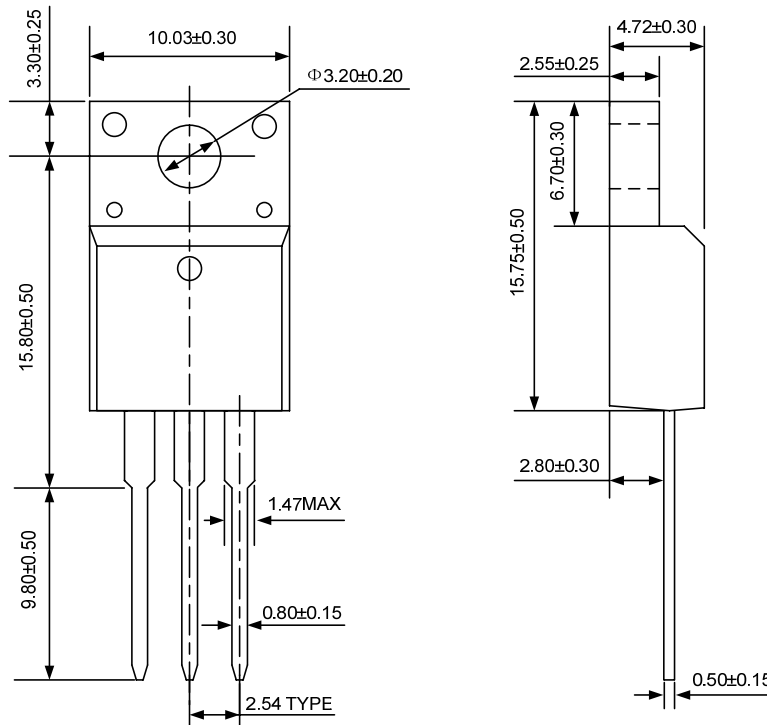
**TO-220-3L**

**UNIT: mm**



**TO-220F-3L**

**UNIT: mm**





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- Silan will supply the best possible product for customers!

## ATTACHMENT

### Revision History

Date	REV	Description	Page
2011.04.28	1.0	Original	